

## **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

Claim 1. (cancelled).

Claim 2. (currently amended) The method of Claim 13, wherein said ~~masking material is~~ blocking layer comprises silicon nitride.

Claim 3. (currently amended) The method of Claim 13, wherein said sidewall spacers consist predominantly of silicon dioxide.

Claim 4. (currently amended) The method of Claim 13, wherein said ~~patterned~~ polysilicon layer is separated from said semiconductor substrate by a gate oxide layer.

Claims 5-12. (cancelled).

Claim 13. (new) A method of forming an integrated circuit, comprising the steps of:  
forming a polysilicon layer over a gate dielectric over a semiconductor substrate;  
forming a blocking layer over said polysilicon layer;  
patterning and etching said polysilicon layer and said blocking layer;  
then, implanting an initial dose of first conductivity type dopant to form source/drain extension regions in said semiconductor substrate;  
then, removing said blocking layer;  
forming sidewall spacers adjacent said polysilicon layer after said step of implanting the initial dose;  
then, with said sidewall spacers present, implanting an additional dose of first conductivity type dopant, with a deeper stopping distance than said implanting an initial dose step, to form main source/drain regions in said semiconductor substrate;

then, depositing a metal layer and reacting said metal layer with portions of said polysilicon layer to form a conductive silicide.